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## SEMICONDUCTOR-BASED **HETEROSTRUCTURES: INTERFACIAL STRUCTURE & STABILITY**

May 1-2, 1986 • AT&T Bell Laboratories, Murray Hill, New Jersey

Approximately 30 papers (9 invited) will be presented at the 1986 Northeast Regional Meeting, addressing Semiconductor-Based Heterostructures and the increasingly significant role they will play in future microelectronic devices.

Presentations in 4 technical sessions will focus on the materials science aspects of interfaces such as perfection, structure and stability, and their relationships to synthesis techniques. Major topics to be highlighted include: Amorphous and Strained-layer superlattices; Si on insulators; Epitaxial Silicides; Compound Semiconductors on Si: Metallization & Passivation of III-V Compounds: Multilevel metallization schemes for VLSI; Nanocomposite materials; Interfacial & Pseudomorphic Growth: Ohmic contact to compound semiconductors: Phase stability; and III-V synthesis (MOCVD vs MBE).

Invited presentations will be:

"Chemical Interactions and Fermi Level Pinning at Metal/III-V Interfaces" L. Brillson, Xerox • "Synthesis of Strained-Layer Superlattices by MOCVD" R. Dupuis, AT&T Bell Labs "Passivation of III-V Compound

- Semiconductors" R. Enstrom, RCA
- "Physical & Chemical Stability of SOI Structures" R.F.C. Farrow, IBM
- "The Formation & Structure of Semiconductor Interfaces Involving Group IV Elements" L.C. Feldman, AT&T Bell Labs
- "Current Status of Schottky-Barrier Formation at Silicide-Silicon Interfaces" P.S. Ho, M. Liehr, IBM
- "Structure & Thermal Relaxation of Amorphous Semiconductor Interfaces" P. Persans, Exxon
- "Heteroepitaxy of GaAs on Si by MBE" G.W. Turner, Lincoln Labs
- "MBE Synthesis of Superlattices" G. Wicks, Cornell

Tutorials and a dinner are being planned to supplement the technical program.

For more information and your advance registration packet, contact:

> **Meetings Department The Metallurgical Society** 420 Commonwealth Drive Warrendale, PA 15086 (412) 776-9050 Telex 910 380 9397



1986 Northeast Regional Meeting is co-sponsored by The Metallurgical Society and the Materials Research Society.

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